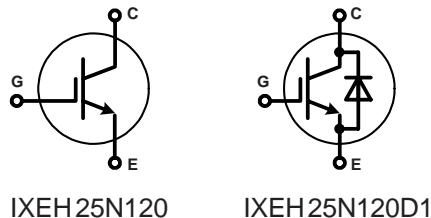
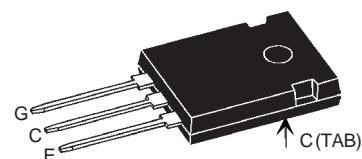


NPT³ IGBT

I_{C25} = 36 A
V_{CES} = 1200 V
V_{CE(sat) typ.} = 2.6 V



TO-247 AD

**IGBT**

Symbol	Conditions	Maximum Ratings		
V _{CES}	T _{VJ} = 25°C to 150°C	1200		V
V _{GES}		± 20		V
I _{C25}	T _C = 25°C	36	A	
I _{C90}	T _C = 90°C	24	A	
I _{CM}	V _{GE} = ±15 V; R _G = 56 Ω; T _{VJ} = 125°C RBSOA, Clamped inductive load; L = 100 μH	40	A	
V _{CEK}				
t _{sc} (SCSOA)	V _{CE} = 900V; V _{GE} = ±15 V; R _G = 56 Ω; T _{VJ} = 125°C non-repetitive	10	μs	
P _{tot}	T _C = 25°C	200		W

Symbol	Conditions	Characteristic Values		
		(T _{VJ} = 25°C, unless otherwise specified)	min.	typ.
V _{CE(sat)}	I _C = 25 A; V _{GE} = 15 V; T _{VJ} = 25°C T _{VJ} = 125°C	2.6 3.2	3.2	V
V _{GE(th)}	I _C = 0.6 mA; V _{GE} = V _{CE}	4.5	6.5	V
I _{CES}	V _{CE} = V _{CES} ; V _{GE} = 0 V; T _{VJ} = 25°C T _{VJ} = 125°C	0.2	0.2	mA
I _{GES}	V _{CE} = 0 V; V _{GE} = ± 20 V		200	nA
t _{d(on)} t _r t _{d(off)} t _f E _{on} E _{off}	Inductive load, T _{VJ} = 125°C V _{CE} = 600 V; I _C = 25 A V _{GE} = ±15 V; R _G = 56 Ω	150	ns	
		60	ns	
		700	ns	
		50	ns	
		3.4	mJ	
		2.5	mJ	
C _{ies} Q _{Gon}	V _{CE} = 25 V; V _{GE} = 0 V; f = 1 MHz V _{CE} = 600 V; V _{GE} = 15 V; I _C = 20 A	1.2 150	nF nC	
R _{thJC}			0.63	K/W

Features

- NPT³ IGBT
 - positive temperature coefficient of saturation voltage for easy paralleling
 - fast switching
 - short tail current for optimized performance in resonant circuits
- optional HiPerFRED™ diode
 - fast reverse recovery
 - low operating forward voltage
 - low leakage current
- TO-247 package
 - industry standard outline
 - epoxy meets UL 94V-0

Applications

- AC drives
- DC drives and choppers
- Uninterruptible power supplies (UPS)
- switched-mode and resonant-mode power supplies
- inductive heating, cookers

Diode [D1 version only]

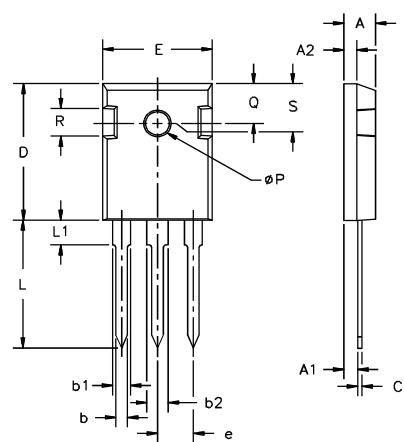
Symbol	Conditions	Maximum Ratings		
I _{F25}	T _C = 25°C	33	A	
I _{F90}	T _C = 90°C	20	A	

Symbol	Conditions	Characteristic Values		
		min.	typ.	max.
V _F	I _F = 25 A; T _{VJ} = 25°C T _{VJ} = 125°C	2.7 2.1	3.2	V
I _{RM} t _{rr}	I _F = 25 A; di _F /dt = -400 A/μs; T _{VJ} = 125°C V _R = 600 V; V _{GE} = 0 V	16 130		A ns
R _{thJC}			1.6	K/W

Component

Symbol	Conditions	Maximum Ratings		
T _{VJ}		-55...+150		°C
T _{stg}		-55...+150		°C
M _d	mounting torque	0.8...1.2		Nm
Symbol	Conditions	Characteristic Values		
		min.	typ.	max.
R _{thCH}	with heatsink compound	0.25		K/W
Weight		6		g

TO-247 AD Outline



Dim.	Millimeter Min.	Millimeter Max.	Inches Min.	Inches Max.
A	4.7	5.3	.185	.209
A ₁	2.2	2.54	.087	.102
A ₂	2.2	2.6	.059	.098
b	1.0	1.4	.040	.055
b ₁	1.65	2.13	.065	.084
b ₂	2.87	3.12	.113	.123
C	.4	.8	.016	.031
D	20.80	21.46	.819	.845
E	15.75	16.26	.610	.640
e	5.20	5.72	.205	.225
L	19.81	20.32	.780	.800
L1		4.50		.177
ØP	3.55	3.65	.140	.144
Q	5.89	6.40	.232	.252
R	4.32	5.49	.170	.216
S	6.15	BSC	.242	BSC